

Panasonic

FL6L52030L

Silicon P-channel MOSFET(FET)

Silicon epitaxial planar type(SBD)

For switching

For DC-DC Converter

■ Features

- Low drain-source ON resistance : $R_{DS(on)}$ typ. = 300 m Ω ($V_{GS} = -4.0$ V)
- Low drive voltage : 2.5 V drive
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol Y3

■ Packaging

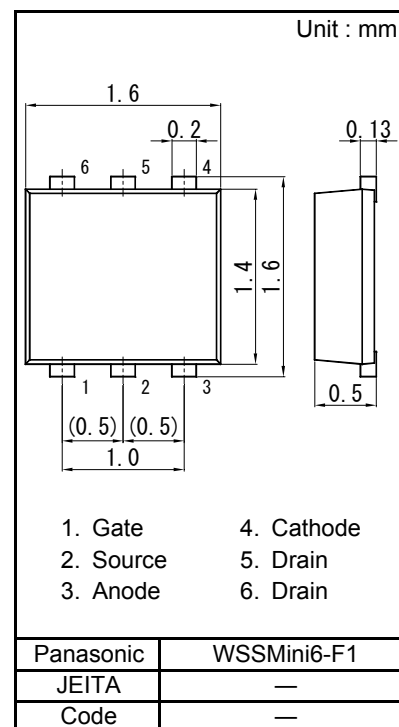
Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

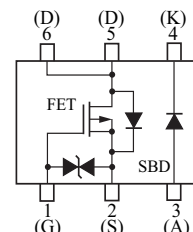
項目		Symbol	Rating	Unit
FET	Drain to Source Voltage	V_{DS}	-20	V
	Gate to Source Voltage	V_{GS}	± 12	V
	Drain current	I_D	-1.0	A
	Peak drain current	I_{Dp}	-4.0	A
	Channel temperature	T_{ch}	150	°C
SBD	Reverse voltage	V_R	20	V
	Forward current (Average)	$I_F(AV)$	800	mA
	Junction temperature	T_j	125	°C
Overall	Total power dissipation ^{*1}	P_D	540	mW
	Operating ambient temperature	T_{opr}	-40 to +85	°C
	Storage temperature	T_{stg}	-55 to +125	°C

Note: *1 Glass epoxy board (25.4 x 25.4 x t0.8 mm) coated with copper foil, which has more than 300mm².

PD absolute maximum rating without a heat sink: 150 mW



Internal Connection



Pin Name

1. Gate 4. Cathode
2. Source 5. Drain
3. Anode 6. Drain